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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Haujie CHEN et al.

Group Art Unit: 2813

Appln. No. : 10/689,506

Examiner: J. M. Mitchell

Filed : October 20, 2003

For : HIGH PERFORMANCE STRESS-ENHANCED MOSFETs USING Si:C
AND SiGe EPITAXIAL SOURCE/DRAIN AND METHOD OF
MANUFACTURE

CHANGE OF CORRESPONDENCE ADDRESS

Commissioner for Patents
U.S. Patent and Trademark Office
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Sir:

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Should there be any questions or comments, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
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